

# FCH47N60F

## 600V N-Channel MOSFET

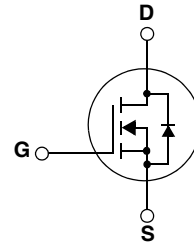
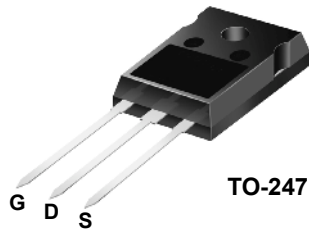
### Features

- 650V @ $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 0.062\Omega$
- Fast Recovery Type (  $t_{rr} = 240\text{ns}$  )
- Ultra Low Gate Charge (typ.  $Q_g = 210\text{nC}$  )
- Low Effective Output Capacitance (typ.  $C_{oss\text{eff.}} = 420\text{pF}$  )
- 100% avalanche tested

### Description

SuperFET™ is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



### Absolute Maximum Ratings

Symbol	Parameter	FCH47N60F	Unit
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	47 29.7	A A
$I_{DM}$	Drain Current - Pulsed (Note 1)	141	A
$V_{GSS}$	Gate-Source voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1800	mJ
$I_{AR}$	Avalanche Current (Note 1)	47	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	41.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	50	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	417 3.33	W W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.3	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	41.7	$^\circ\text{C/W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH47N60F	FCH47N60F	TO-247	-	-	30

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

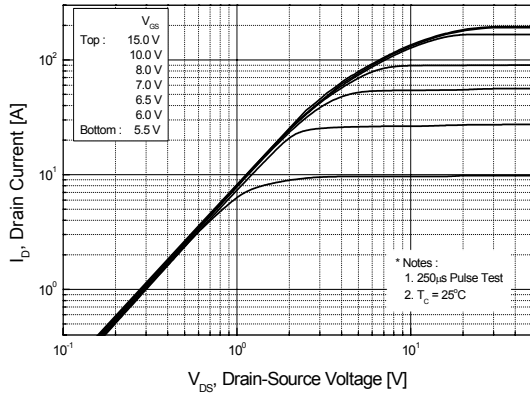
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA, T <sub>J</sub> = 25°C	600	--	--	V
		V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA, T <sub>J</sub> = 150°C	--	650	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	--	0.6	--	V/°C
BV <sub>DS</sub>	Drain-Source Avalanche Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 47A	--	700	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 480V, T <sub>C</sub> = 125°C	--	--	10 100	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 23.5A	--	0.062	0.073	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40V, I <sub>D</sub> = 23.5A (Note 4)	--	40	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	--	5900	8000	pF
C <sub>oss</sub>	Output Capacitance		--	3200	4200	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	250	--	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 480V, V <sub>GS</sub> = 0V, f = 1.0MHz	--	160	--	pF
C <sub>oss eff.</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0V to 400V, V <sub>GS</sub> = 0V	--	420	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 300V, I <sub>D</sub> = 47A R <sub>G</sub> = 25Ω	--	185	430	ns
t <sub>r</sub>	Turn-On Rise Time		--	210	450	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	520	1100	ns
t <sub>f</sub>	Turn-Off Fall Time		(Note 4, 5)	--	75	160
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 480V, I <sub>D</sub> = 47A V <sub>GS</sub> = 10V	--	210	270	nC
Q <sub>gs</sub>	Gate-Source Charge		--	38	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		(Note 4, 5)	--	110	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	47	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	141	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 47A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 47A di <sub>F</sub> /dt = 100A/μs (Note 4)	--	240	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	2.04	--	μC

### NOTES:

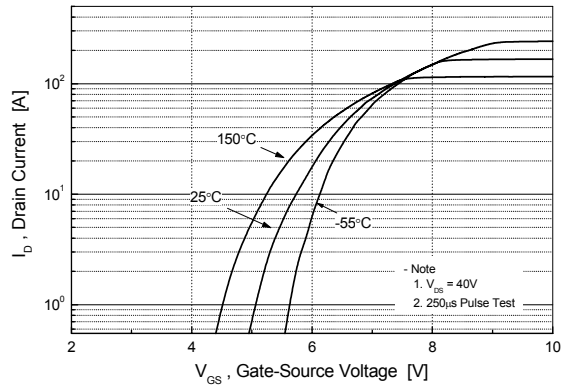
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I<sub>AS</sub> = 18A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 47A, di<sub>F</sub>/dt ≤ 1,200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

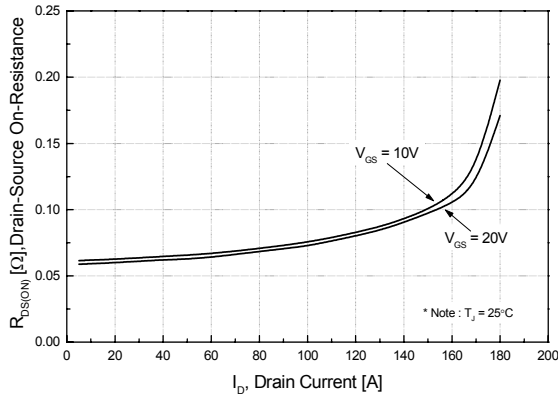
**Figure 1. On-Region Characteristics**



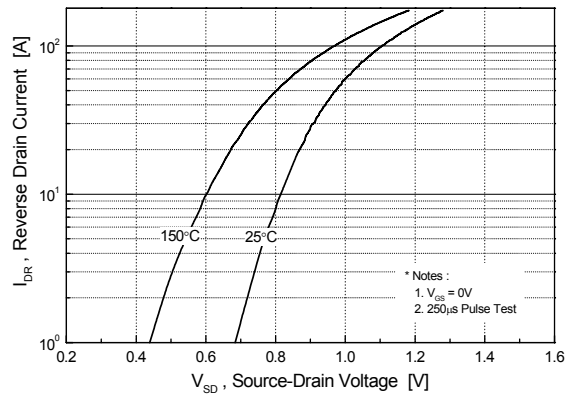
**Figure 2. Transfer Characteristics**



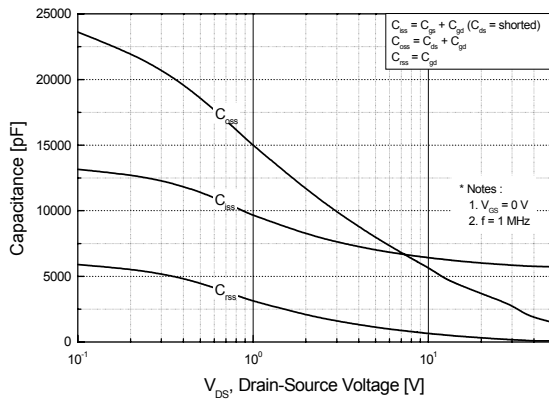
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



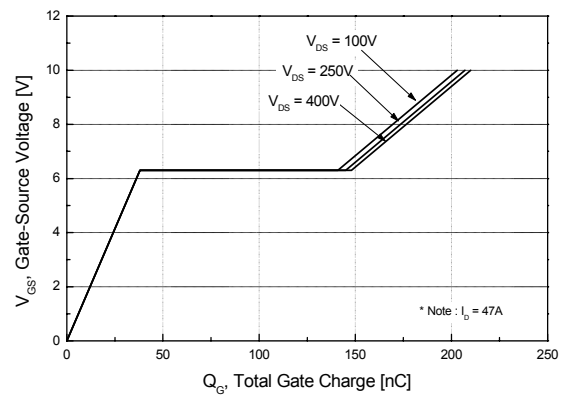
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

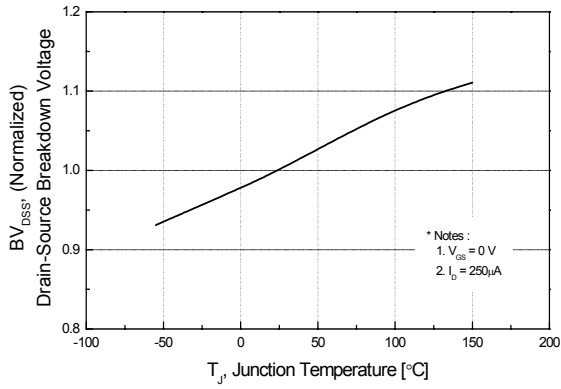


**Figure 6. Gate Charge Characteristics**

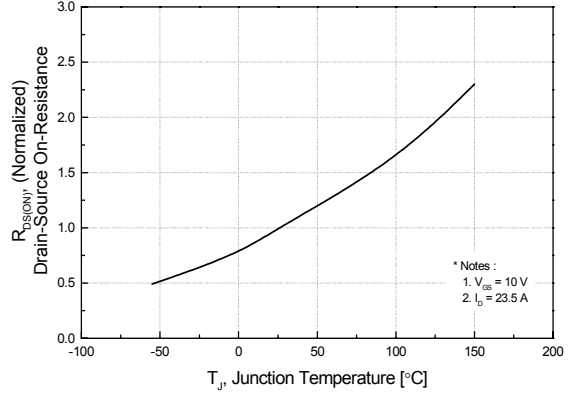


## Typical Performance Characteristics (Continued)

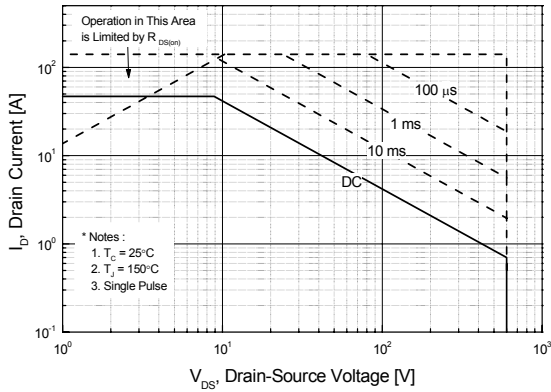
**Figure 7. Breakdown Voltage Variation vs. Temperature**



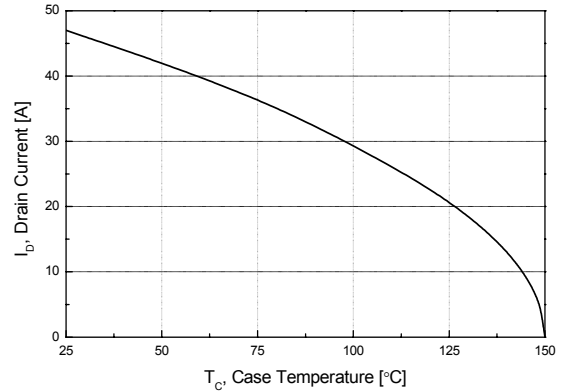
**Figure 8. On-Resistance Variation vs. Temperature**



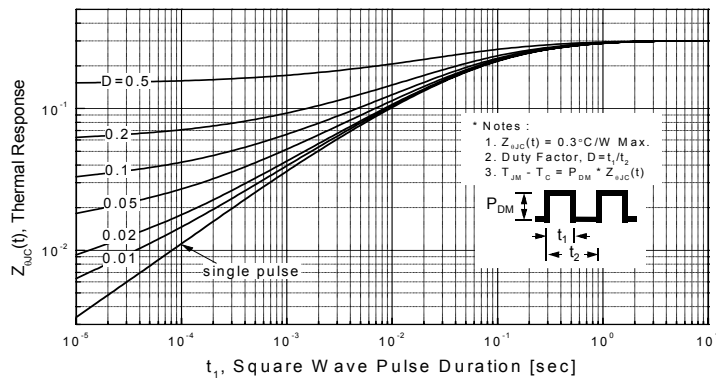
**Figure 9. Safe Operating Area**



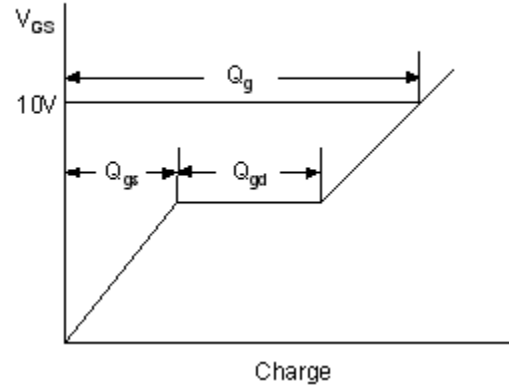
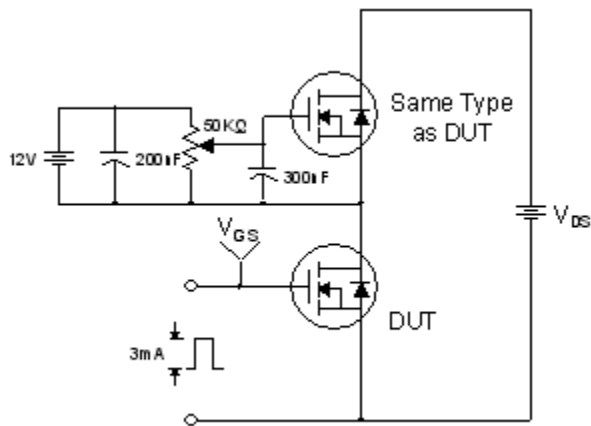
**Figure 10. Maximum Drain Current vs. Case Temperature**



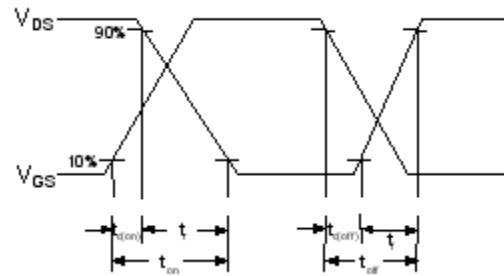
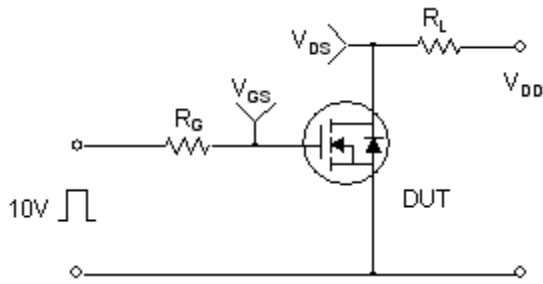
**Figure 10. Transient Thermal Response Curve**



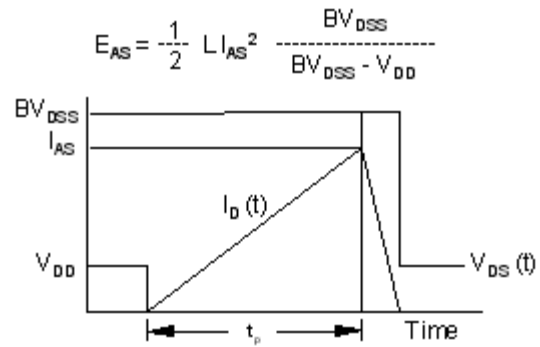
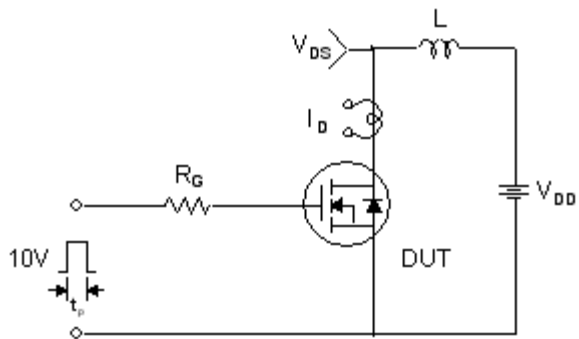
**Gate Charge Test Circuit & Waveform**



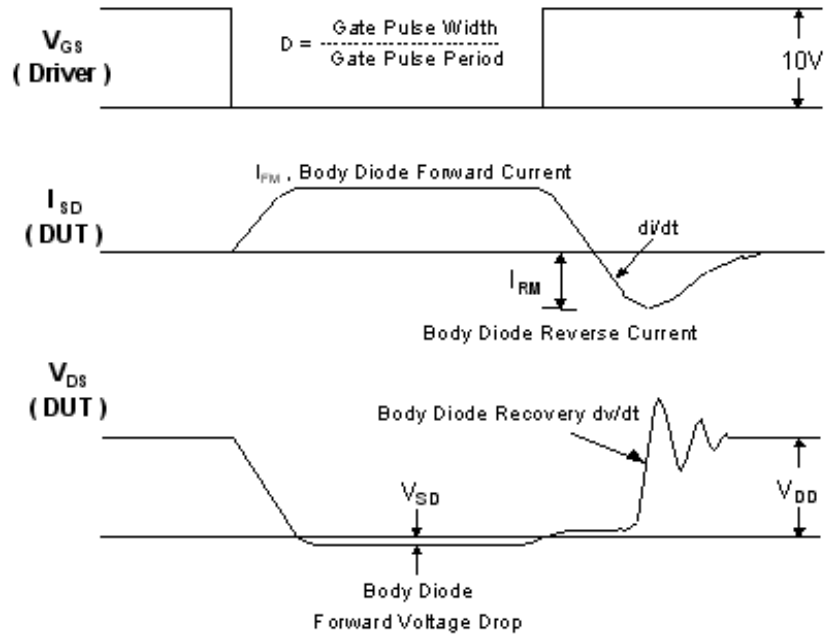
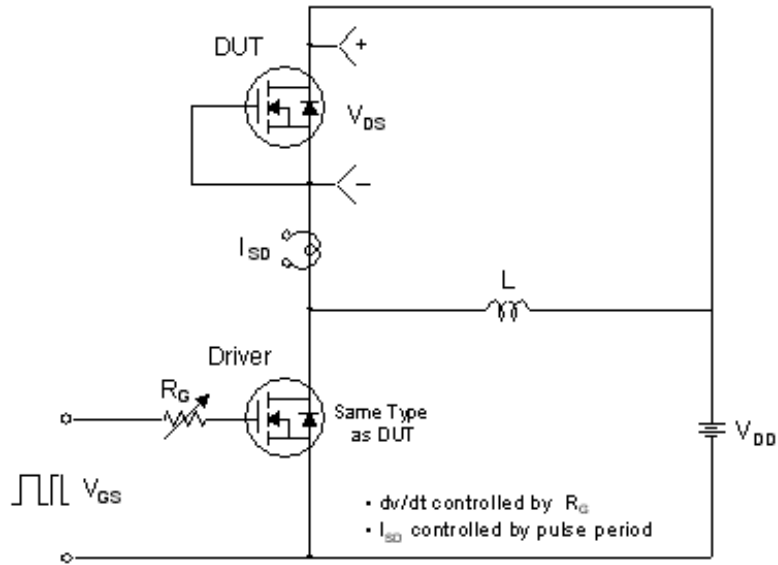
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

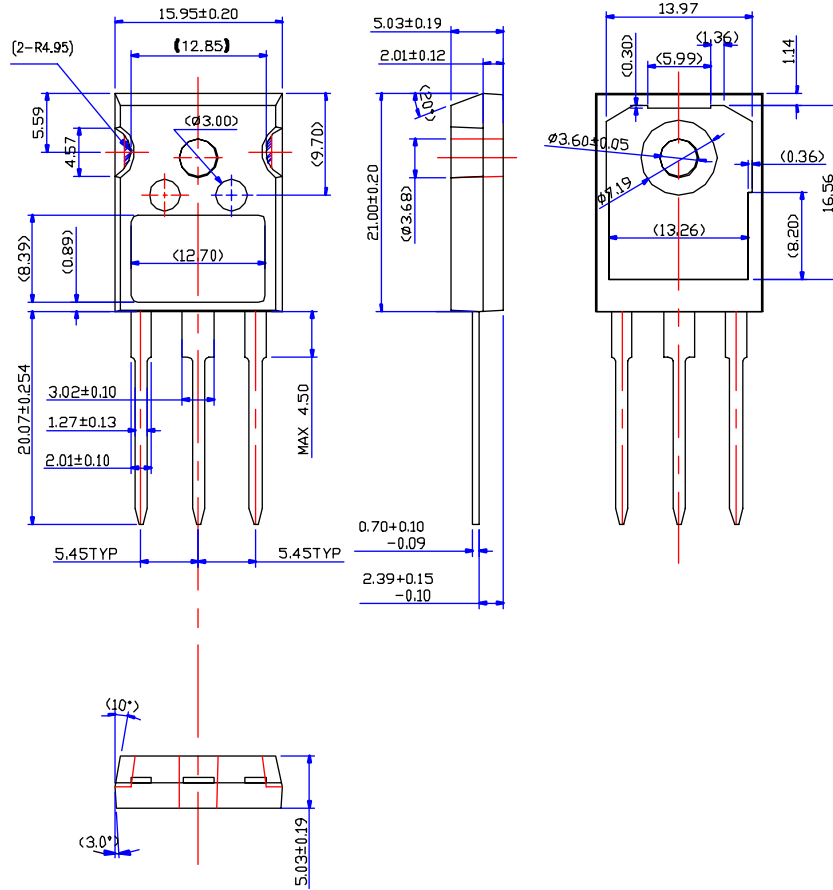


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-247AD (FKS PKG CODE 001)



Dimensions in Millimeters

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DOMET™	HiSeC™	MSX™	Quiet Series™	TinyLogic®
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E <sup>2</sup> CMOS™	i-Lo™	OCX™	RapidConnect™	TruTranslation™
EnSigna™	ImpliedDisconnect™	OCXPro™	µSerDes™	UHC™
FACT™	IntelliMAX™	OPTOLOGIC®	ScalarPump™	UltraFET®
FACT Quiet Series™		OPTOPLANAR™	SILENT SWITCHER®	UniFET™
Across the board. Around the world.™		PACMAN™	SMART START™	VCX™
The Power Franchise®		POP™	SPM™	Wire™
Programmable Active Droop™		Power247™	Stealth™	

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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